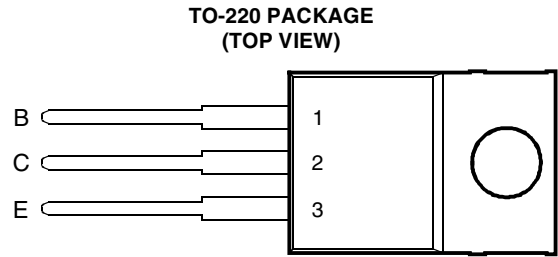


- Rugged Triple-Diffused Planar Construction
- 4 A Continuous Collector Current
- Operating Characteristics Fully Guaranteed at 100°C
- 1200 Volt Blocking Capability
- 75 W at 25°C Case Temperature



Pin 2 is in electrical contact with the mounting base.

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absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ($I_E = 0$)	TIPL760B	V_{CBO}	1100	V
	TIPL760C		1200	
Collector-emitter voltage ($V_{BE} = 0$)	TIPL760B	V_{CES}	1100	V
	TIPL760C		1200	
Collector-emitter voltage ($I_B = 0$)	TIPL760B	V_{CEO}	500	V
	TIPL760C		550	
Emitter-base voltage		V_{EBO}	10	V
Continuous collector current		I_C	4	A
Peak collector current (see Note 1)		I_{CM}	8	A
Continuous device dissipation at (or below) 25°C case temperature		P_{tot}	75	W
Operating junction temperature range		T_j	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C

NOTE 1: This value applies for $t_p \leq 10$ ms, duty cycle $\leq 2\%$.

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electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{CE(sus)}$	Collector-emitter sustaining voltage	$I_C = 10 \text{ mA}$	$L = 25 \text{ mH}$	(see Note 2)	TIPL760B TIPL760C	500 550		V
I_{CES}	Collector-emitter cut-off current	$V_{CE} = 1100 \text{ V}$	$V_{BE} = 0$		TIPL760B		50	μA
		$V_{CE} = 1200 \text{ V}$	$V_{BE} = 0$		TIPL760C		50	
		$V_{CE} = 1100 \text{ V}$	$V_{BE} = 0$	$T_C = 100^\circ\text{C}$	TIPL760B		200	
		$V_{CE} = 1200 \text{ V}$	$V_{BE} = 0$	$T_C = 100^\circ\text{C}$	TIPL760C		200	
I_{CEO}	Collector cut-off current	$V_{CE} = 500 \text{ V}$	$I_B = 0$		TIPL760B		50	μA
		$V_{CE} = 550 \text{ V}$	$I_B = 0$		TIPL760C		50	
I_{EBO}	Emitter cut-off current	$V_{EB} = 10 \text{ V}$	$I_C = 0$				1	mA
h_{FE}	Forward current transfer ratio	$V_{CE} = 5 \text{ V}$	$I_C = 0.5 \text{ A}$	(see Notes 3 and 4)		20	60	
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_B = 0.4 \text{ A}$	$I_C = 2 \text{ A}$				1.0	V
		$I_B = 0.6 \text{ A}$	$I_C = 3 \text{ A}$	(see Notes 3 and 4)			2.5	
		$I_B = 0.6 \text{ A}$	$I_C = 3 \text{ A}$	$T_C = 100^\circ\text{C}$			5.0	
$V_{BE(sat)}$	Base-emitter saturation voltage	$I_B = 0.4 \text{ A}$	$I_C = 2 \text{ A}$				1.2	V
		$I_B = 0.6 \text{ A}$	$I_C = 3 \text{ A}$	(see Notes 3 and 4)			1.4	
		$I_B = 0.6 \text{ A}$	$I_C = 3 \text{ A}$	$T_C = 100^\circ\text{C}$			1.3	
f_t	Current gain bandwidth product	$V_{CE} = 10 \text{ V}$	$I_C = 0.5 \text{ A}$	$f = 1 \text{ MHz}$			12	MHz
C_{ob}	Output capacitance	$V_{CB} = 20 \text{ V}$	$I_E = 0$	$f = 0.1 \text{ MHz}$			110	pF

- NOTES: 2. Inductive loop switching measurement.
 3. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.
 4. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			1.56	$^\circ\text{C/W}$

inductive-load-switching characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t_{sv}	Voltage storage time	$I_C = 3 \text{ A}$ $V_{BE(off)} = -5 \text{ V}$	$I_{B(on)} = 0.6 \text{ A}$	(see Figures 1 and 2)			2.5	μs
t_{rv}	Voltage rise time						300	ns
t_{fi}	Current fall time						250	ns
t_{ti}	Current tail time						150	ns
t_{xo}	Cross over time						400	ns
t_{sv}	Voltage storage time				$I_C = 3 \text{ A}$ $V_{BE(off)} = -5 \text{ V}$	$I_{B(on)} = 0.6 \text{ A}$ $T_C = 100^\circ\text{C}$	(see Figures 1 and 2)	
t_{rv}	Voltage rise time			500				ns
t_{fi}	Current fall time			250				ns
t_{ti}	Current tail time			150				ns
t_{xo}	Cross over time			750				ns

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN
VS
COLLECTOR CURRENT

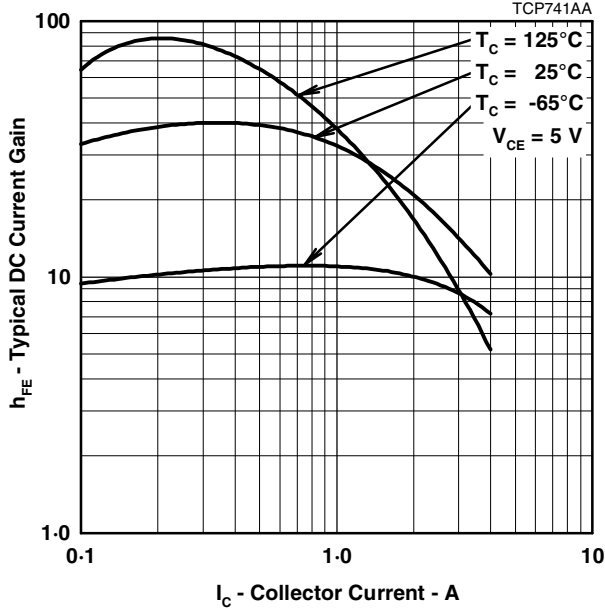


Figure 3.

COLLECTOR-EMITTER SATURATION VOLTAGE
VS
BASE CURRENT

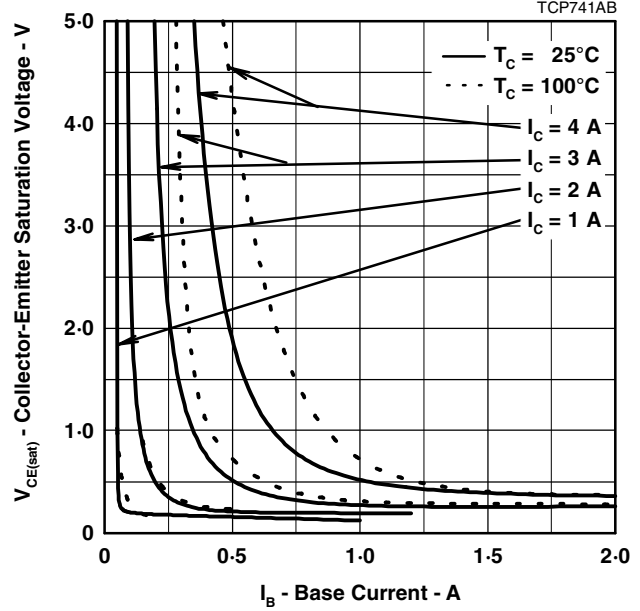


Figure 4.

BASE-EMITTER SATURATION VOLTAGE
VS
BASE CURRENT

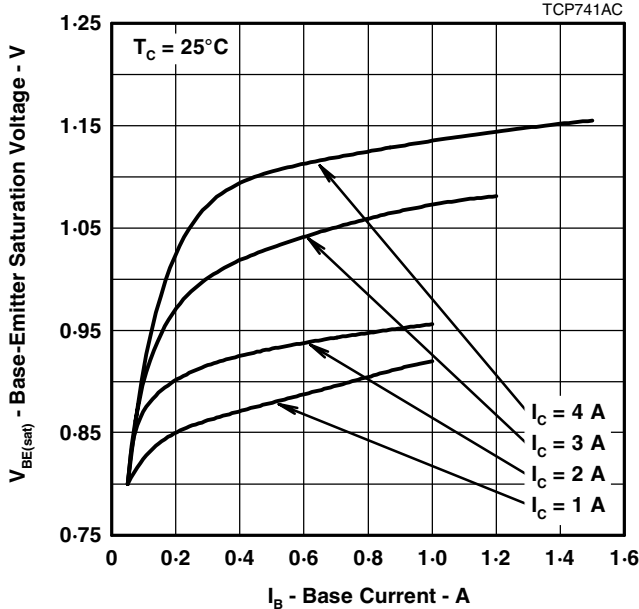


Figure 5.

COLLECTOR CUT-OFF CURRENT
VS
CASE TEMPERATURE

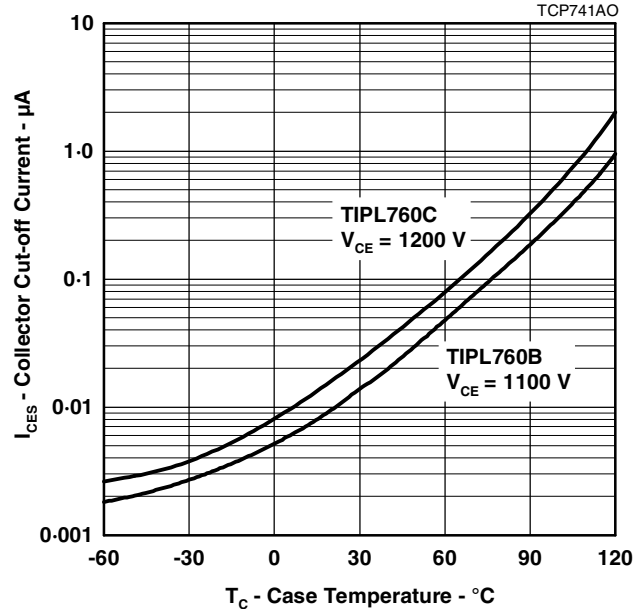


Figure 6.

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MAXIMUM SAFE OPERATING REGIONS

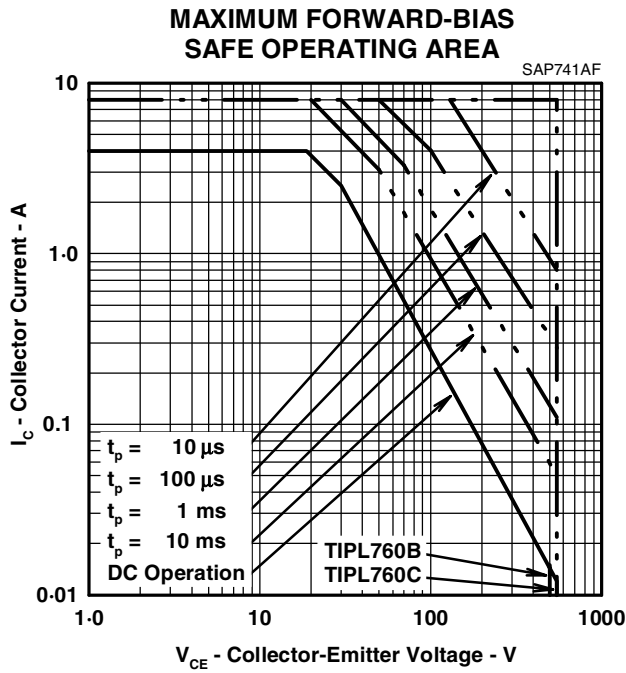


Figure 7.

THERMAL INFORMATION

**THERMAL RESPONSE JUNCTION TO CASE
VS
POWER PULSE DURATION**

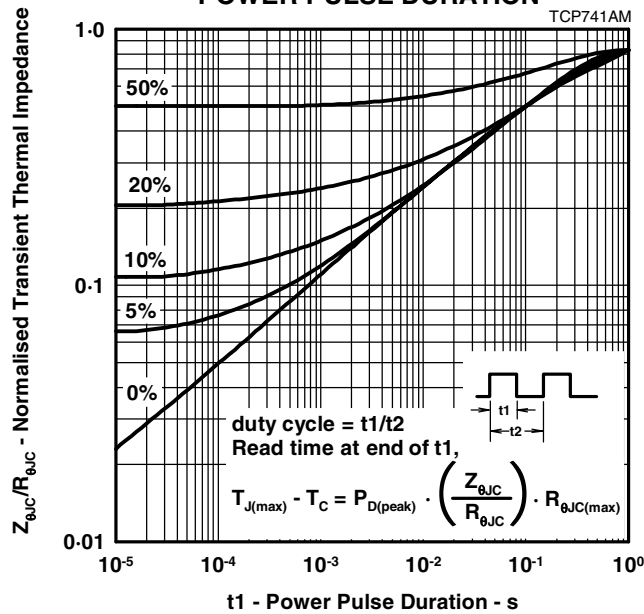


Figure 8.

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